NSN 5961-01-219-4517

Semiconductor Device Set - Page 1 of 1



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Inclosure Material:

Ceramic all semiconductor device diode

Overall Length:

0.190 inches all semiconductor device diode and 0.210 inches all semiconductor device diode

Overall Diameter:

0.078 inches all semiconductor device diode and 0.084 inches all semiconductor device diode

Component Function Relationship:

Matched

Component Name And Quantity:

2 semiconductor device diode

Mounting Method:

Compression all semiconductor device diode

Field Force Effect Type:

Electrostatic charge

Semiconductor Material:

Silicon all semiconductor device diode

Voltage Rating In Volts Per Characteristic:

2.0 reverse voltage, instantaneous all semiconductor device diode

Current Rating Per Characteristic:

40.00 milliamperes source cutoff current preset all semiconductor device diode

Power Rating Per Characteristic:

110.0 milliwatts small-signal input power, common-collector absolute all semiconductor device diode

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Precious Material And Location:

Contact surfaces plated gold

Test Data Document:

96214-775085 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

2 ferrule all semiconductor device diode

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A110a0